EE2 Midterm Examination Prof. H. R. Fetterman 11/9/04 1 and 1/3 hours Closed Book.

Please do all work on separate sheets

1a.For the indicated planes find the Miller indices. Please show your work.

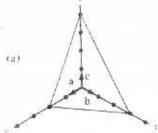
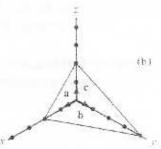


Figure 1



1b. In the Figure 2 below an electron is in a two dimensional box with the Ψ_x wavefunction corresponding to an energy of 4 eV.

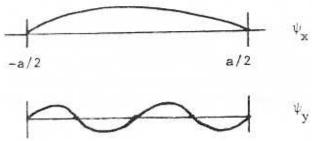


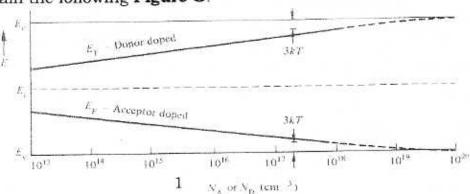
Figure 2 What is the total energy of this 2D system? If the Ψ_x wavefunction was raised to an n = 3 level what would be the total energy?

1c. An energy band is approximated by the expression:

 $E(k) = (h^2k^2/2m_0) - Ak^4$

Using the condition that $\mathbf{v_g} = \mathbf{0}$ at $\mathbf{k} = \pi/a$ calculate A. Also calculate \mathbf{m}^* when $\mathbf{k} = \mathbf{0}$ and $\mathbf{k} = \pi/a$. What is the value of k for which $\mathbf{v_g}$ is maximum?

2a. Using the equations for n and n_i write an expression for the difference between the Fermi level $(\mathbf{E_F})$ and the intrinsic Fermi energy $(\mathbf{E_i})$ in n type material. Explain the following **Figure 3**.



2b. Write the expression for charge neutrality keeping both terms N_D and N_A . Now solve the resulting quadratic equation to find an expression for \mathbf{n} . Show that in a compensated \mathbf{n} type (large N_D and N_A) the minority hole concentration: $\mathbf{p_{no}} = \mathbf{n_{i}}^2 / \mathbf{n_{no}} = \mathbf{n_{i}}^2 / (N_D - N_A)$

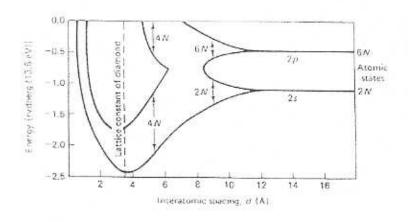
2c. Explain why **As** is a donor in **Si material** and why **Ga** is a acceptor in **Si material**. Now explain what would happen if **Si** atoms were introduced into **GaAs** material.

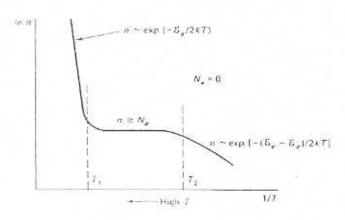
In terms of the donor atoms estimate their **ionization energy** if the dielectric constant of the material is 10 and the effective mass of an electron is $0.5m_0$.

3a. Using the density of state function Z(p) find the average p at T=0 in terms of p_F . Now derive an expression for the average value of p^2 . What is the average kinetic energy based upon this value?

3b. Convert the density of electrons, per unit volume, **Z(p)dp** to a function of energy **Z(E)dE**. Now derive the total number of electrons (n), per unit volume, in a metal as a function of the Fermi energy at T = 0. Write an expression for the Fermi energy as a function of n. How would the Fermi Energy change if the effective mass was reduced by a factor of 2?

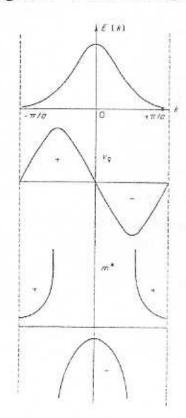
3c. Finally, please explain the following diagrams in Figure 4, and the equations, in no more than three sentences each.



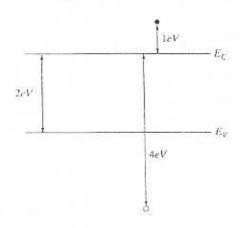


(b)

(c) Explain the motion of an electron starting at k=0 and moving to π/a



(d) Which Carrier has larger Kinetic energy



$$Z(E) = \frac{4\pi V(2m)^{\frac{3}{8}}}{h^3} E^{\frac{1}{8}}$$

$$Z(P) dp = 8\pi p^2 dp V/h^3$$

$$R = \frac{2v_0^3}{h^3} \int_{V_X} \int_{V_Y} \int_{V_Z} \epsilon_0(v_x v_y, v_z) dv_x dv_y$$

$$dN_p = Z(p) dp f(E) = \frac{8\pi V}{h^3} \int_{\frac{E-E_F}{kT}+1} p^2 dp$$

$$v = \frac{1}{4} \int_{\frac{E-E_F}{kT}+1} p$$